

Fig. 1 (a)

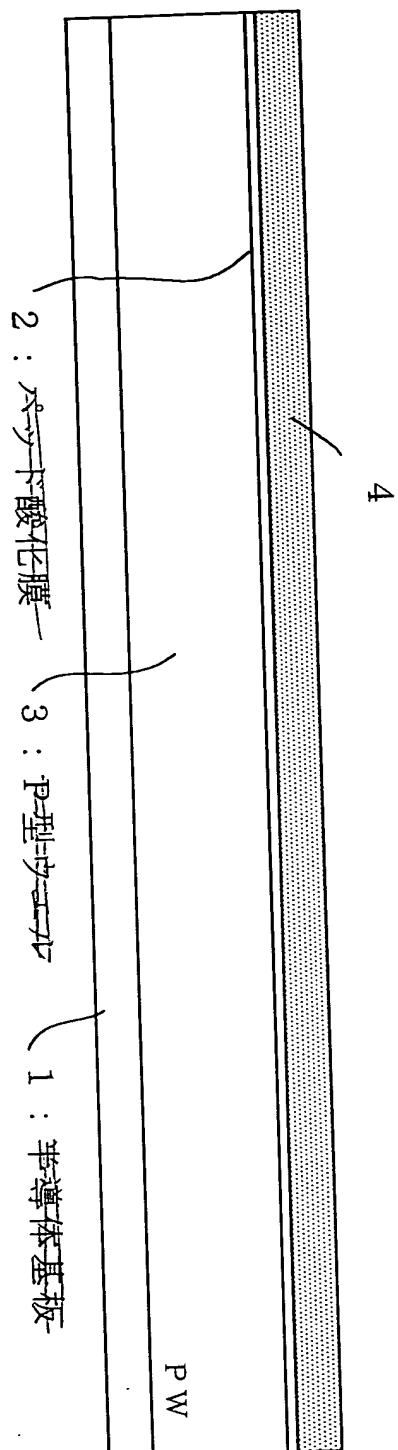


Fig. 1 (b)

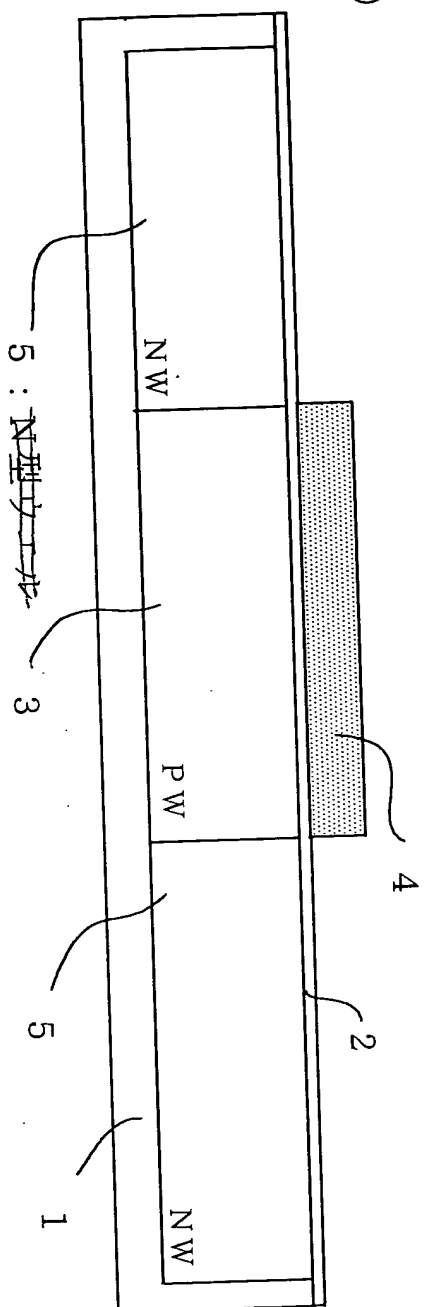


Fig. 3 (a)

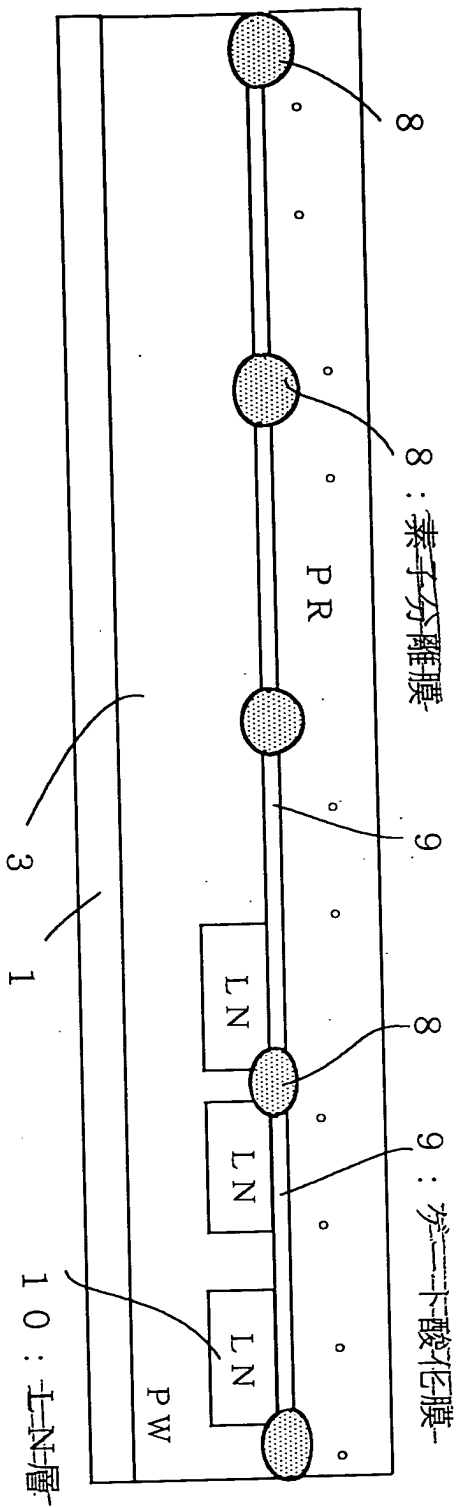


Fig. 3 (b)

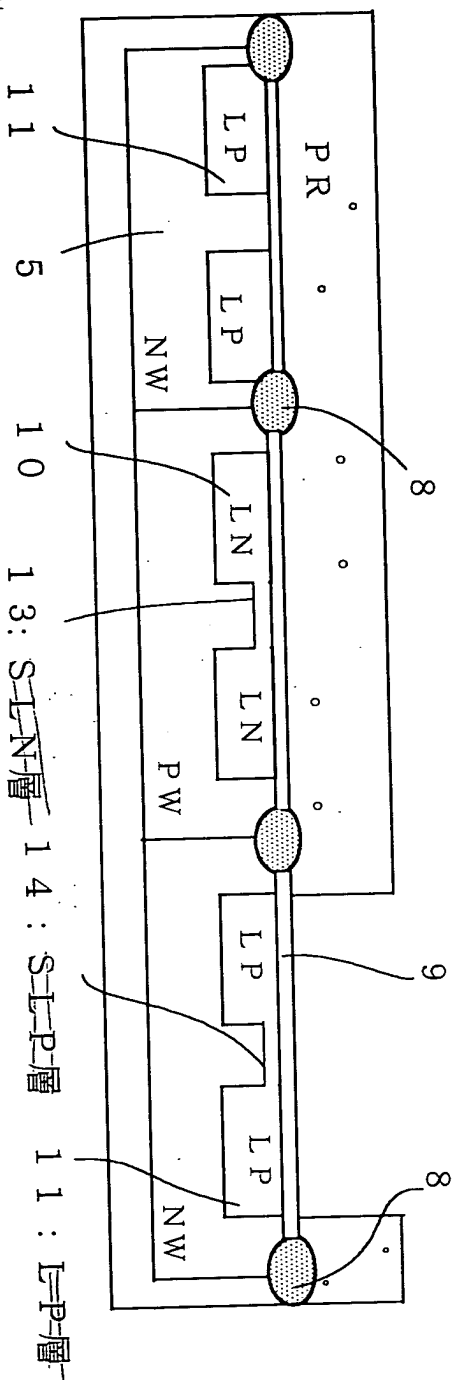


Fig. 4(a)

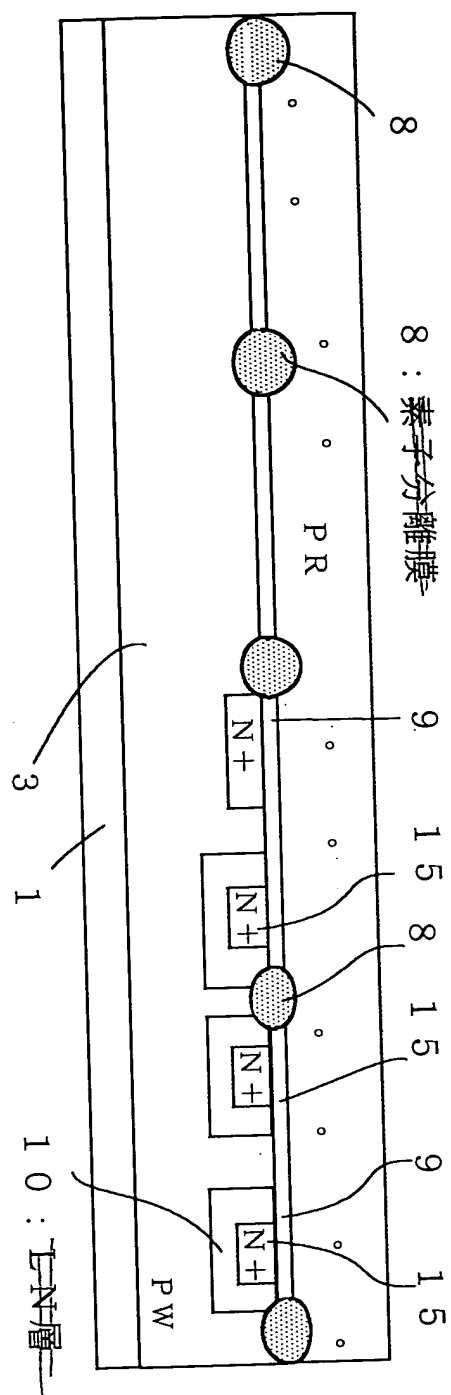
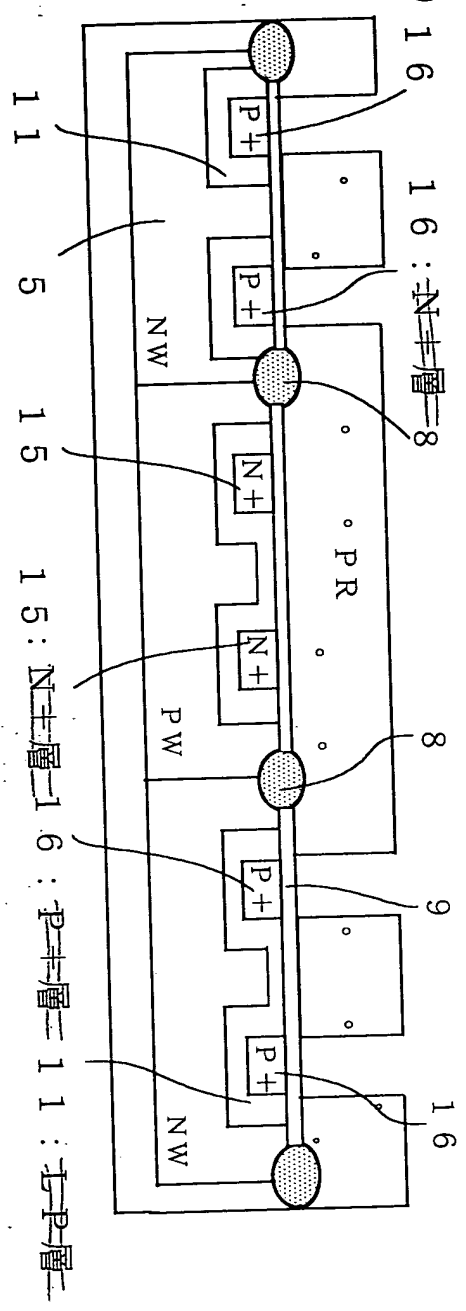


Fig. 4(b)



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Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate with a central channel. The channel contains a series of circular contacts (8) and rectangular regions (9, 15). The regions are labeled with 'N+' and 'P+' symbols. A P-type region (PR) is also indicated.

This diagram shows a cross-sectional view of a semiconductor device. A central channel region is labeled PR . It is flanked by two main gate regions, 16 on the left and 19 on the right. The channel is divided into several segments by vertical dividers. The segments are labeled with their respective regions: $P+$, $N+$, P , $N+$, $P+$, and N . The dividers are labeled NW and PW . The top surface of the device is labeled 11 . The bottom surface is labeled 15 . The central channel is labeled 8 . The rightmost gate region is labeled 9 . The rightmost segment is labeled $18:P/N$. The rightmost divider is labeled 15 . The rightmost gate region is labeled 16 . The rightmost segment is labeled 16 . The rightmost divider is labeled 16 .

21:第2Pウェル 22:第2Nウェル 3 1

16 16 8 8 9 19 16

11 5 15 18 15 16 16

P+ P+ N+ P N+ P+ N P+

NW PW PR



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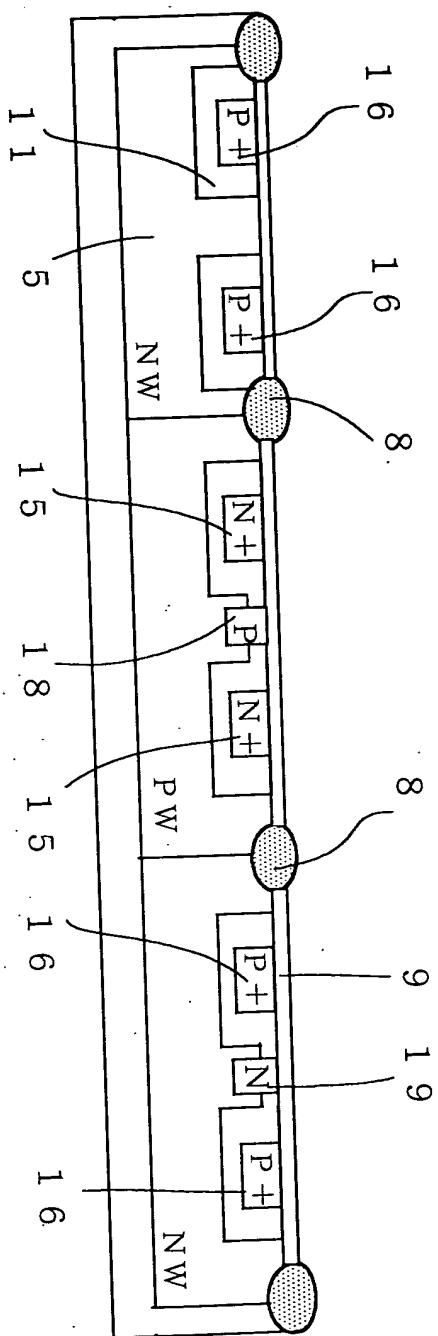


Fig. 8 (a)

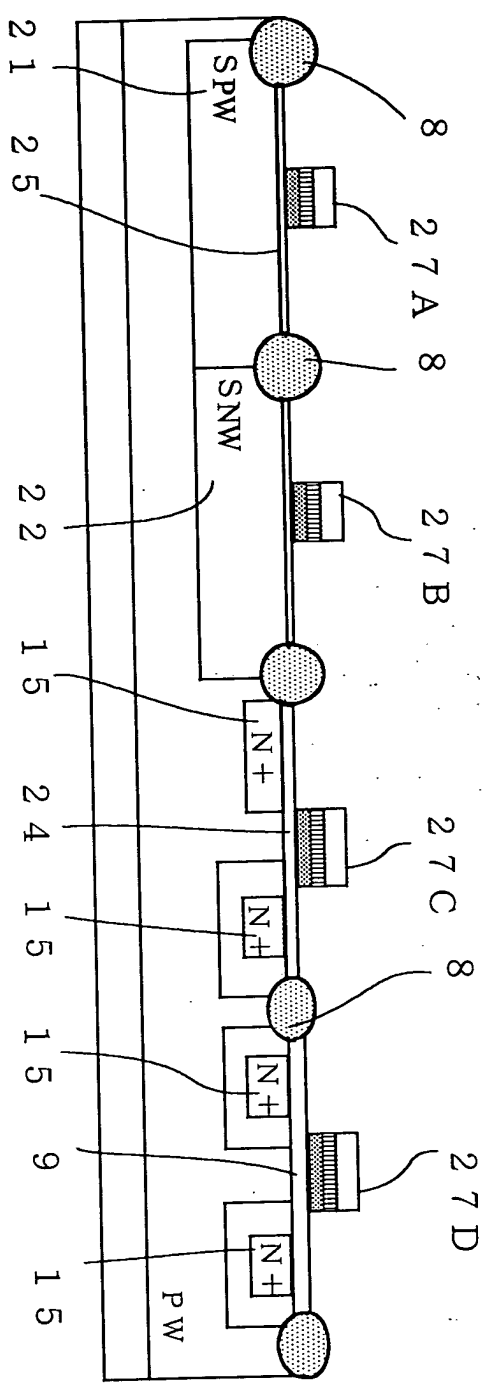
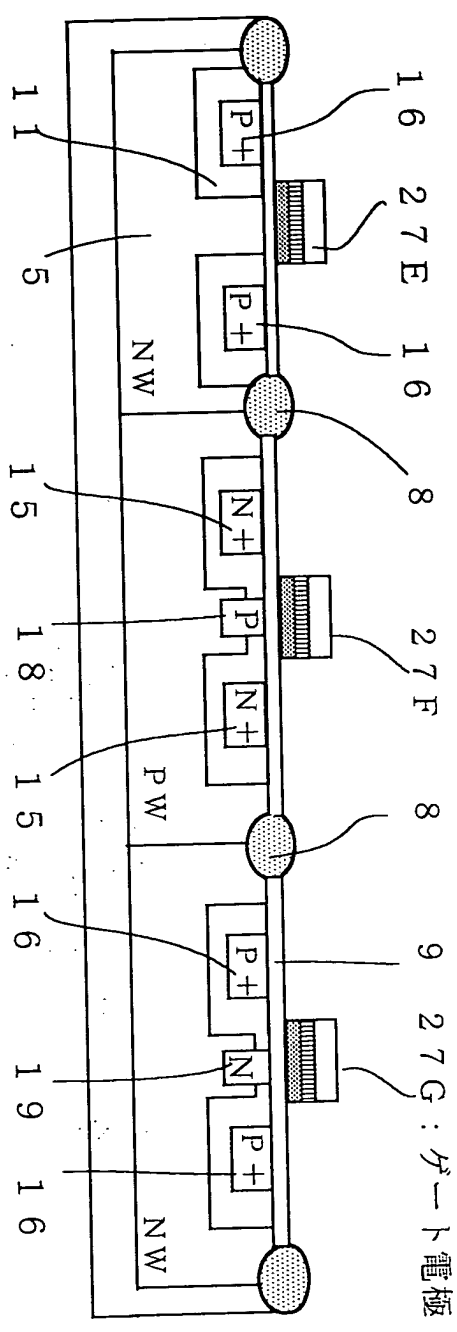


Fig. 8 (b)



335044 033400

(a)



(b)

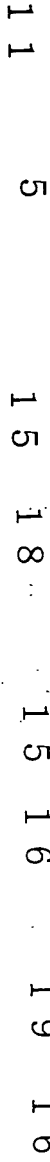


Fig. 10 (a)

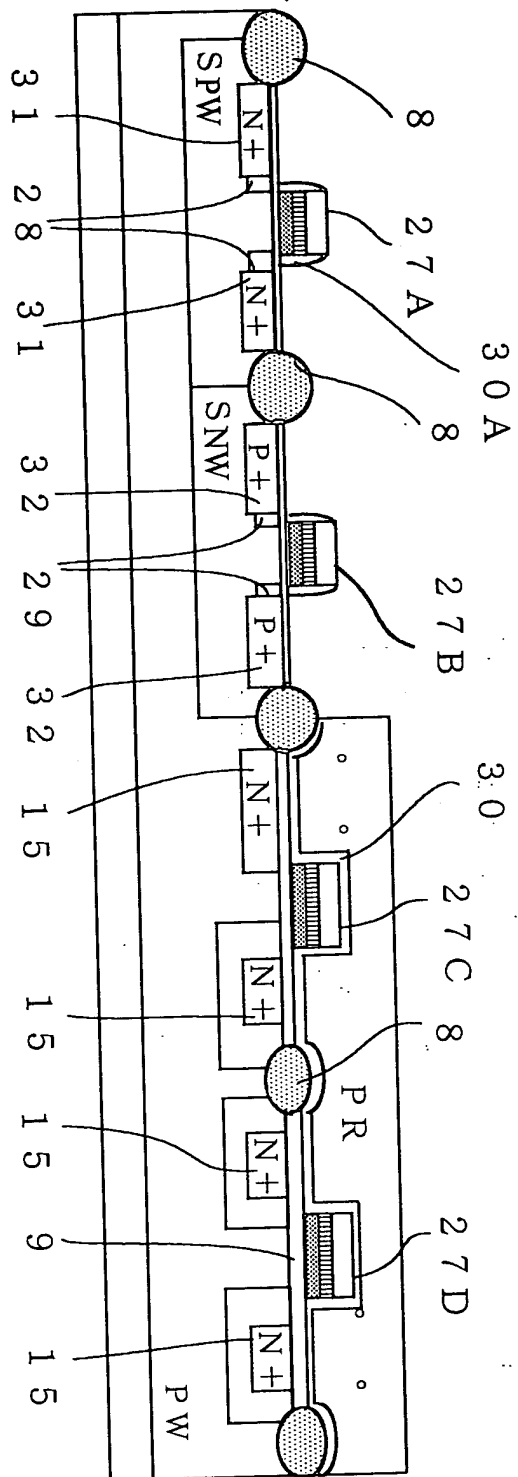


Fig. 10 (b)

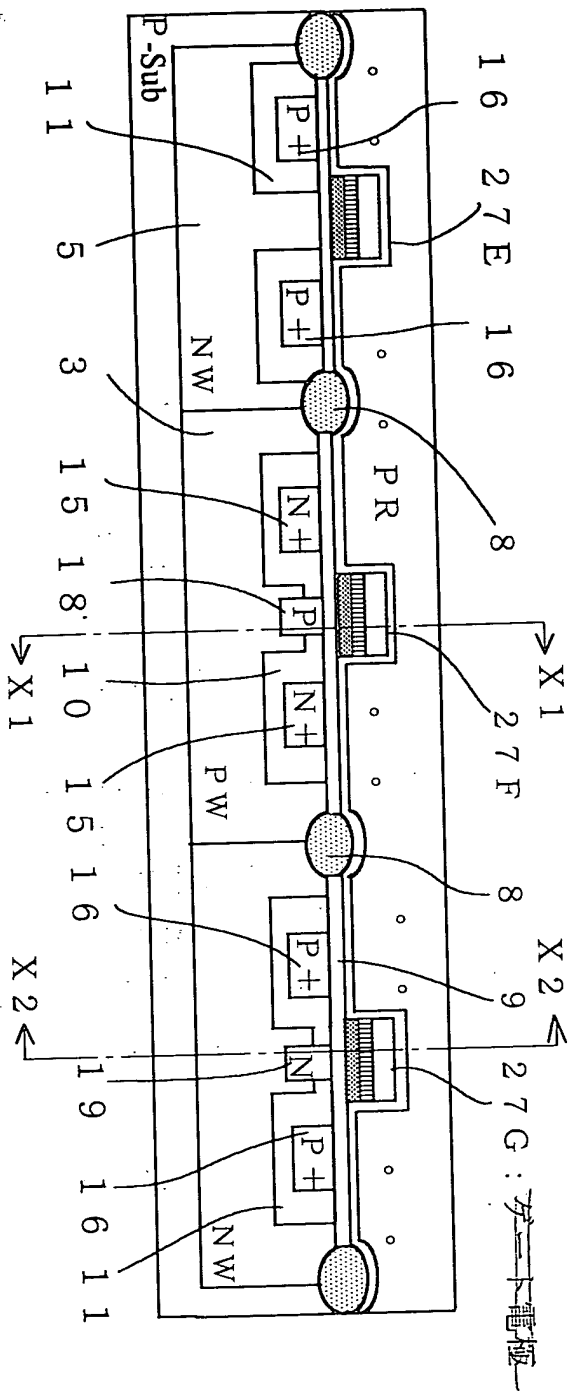


Fig. 11 (a)

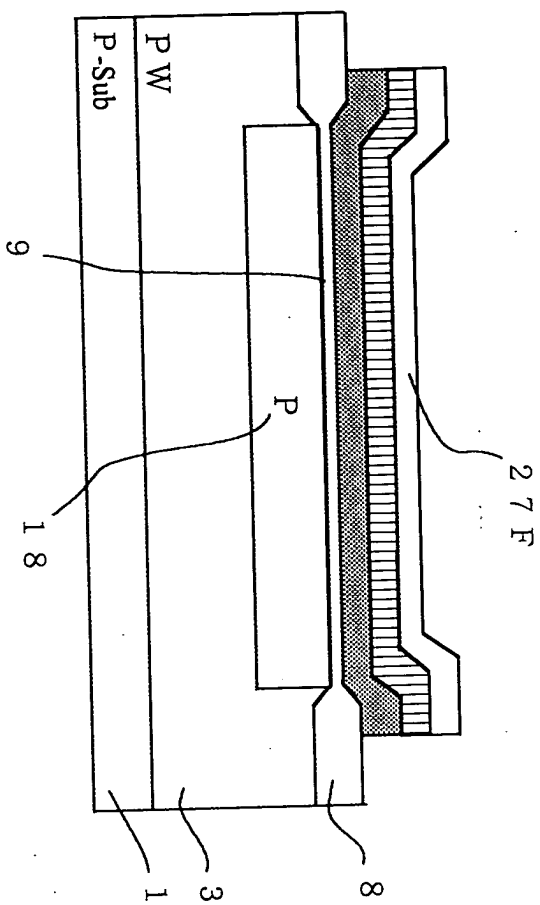


Fig. 11 (b)

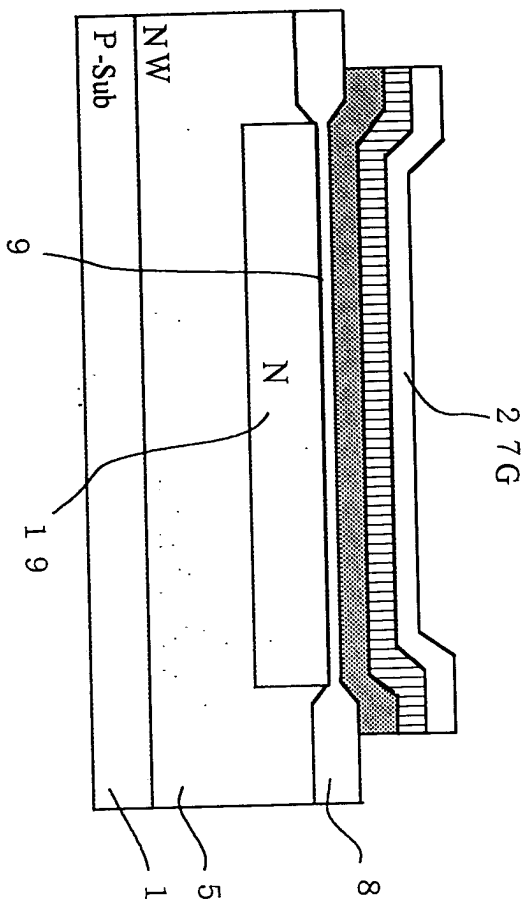


Fig. 12 (a)

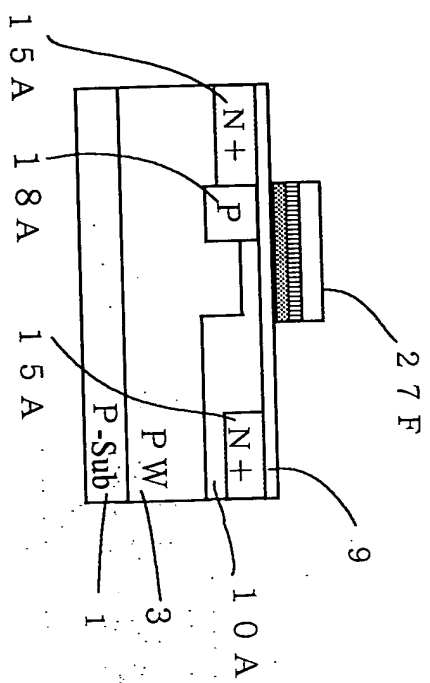
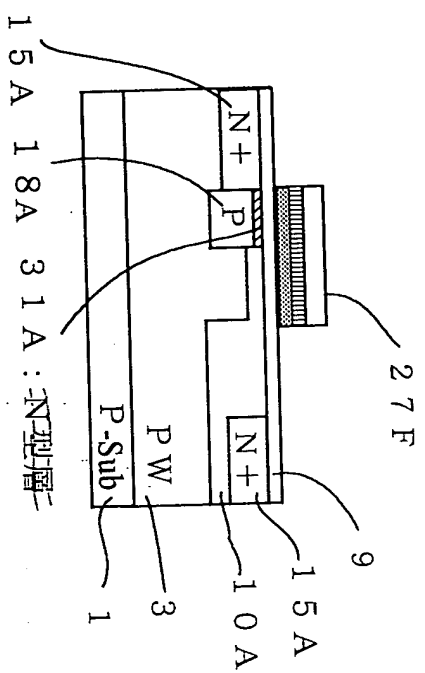
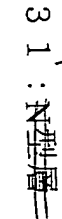


Fig. 12 (b)



(a)

 (q) 

